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Si vs SiC Power modules in HEV integration: a cost point of view

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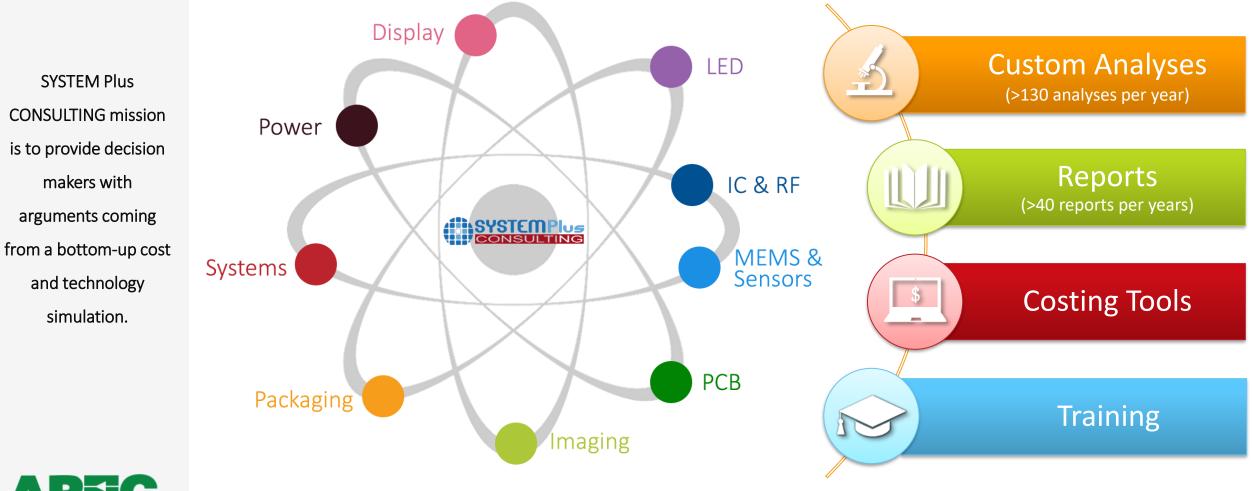
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Business Models and Fields of Expertise



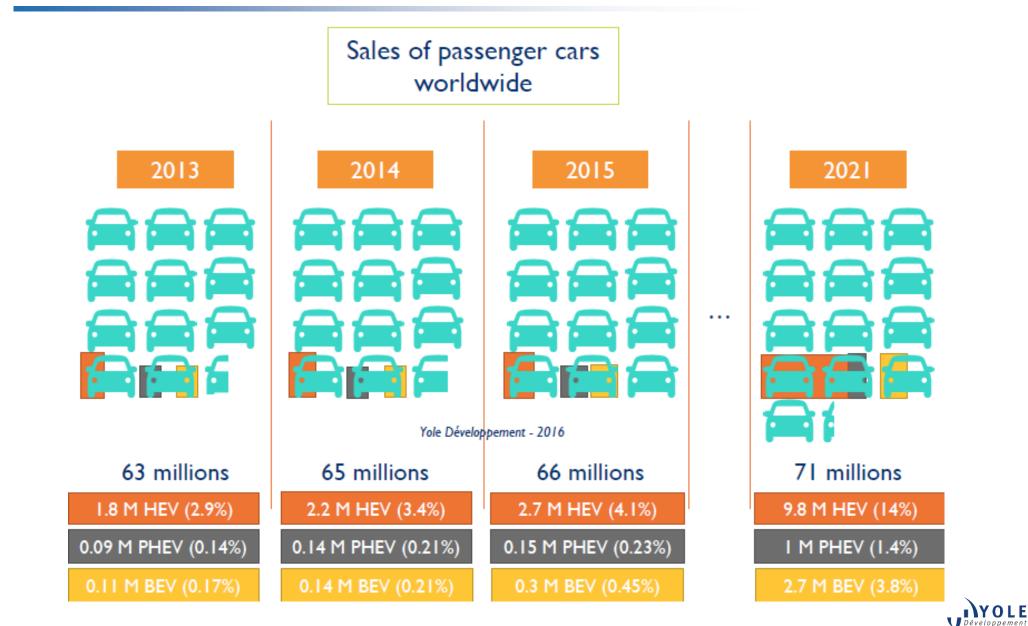




EV/HEV Market

Between 2014 and 2015, the amount of full electric cars sold was multiplied by 2, which is very encouraging for the future By 2021, we expect electrified cars to represent almost 20% of the sales





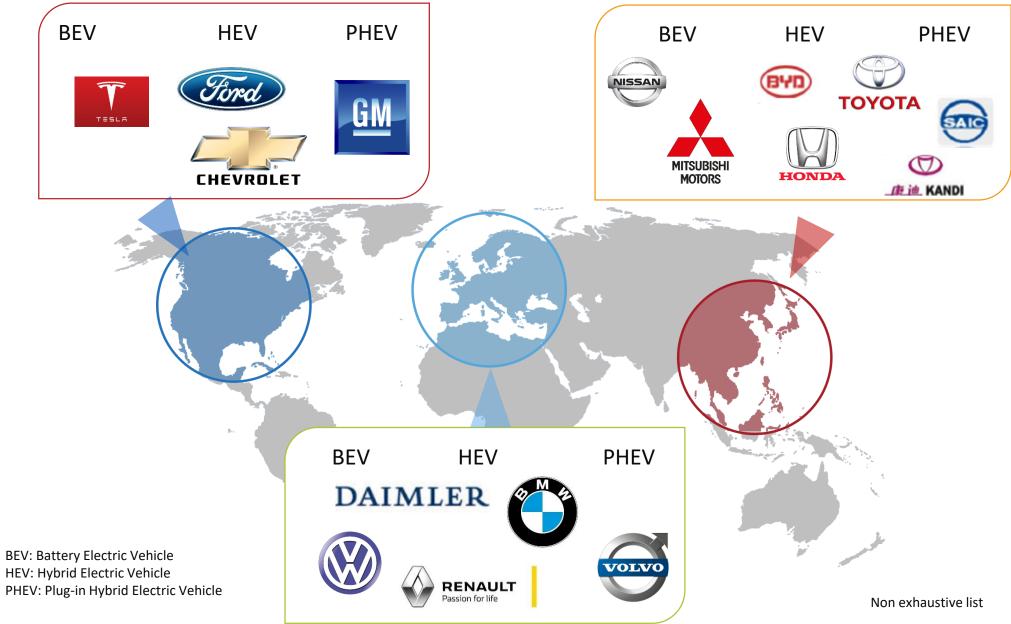
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EV/HEV Main Manufacturers

Electrification trends depend on the strategy of local car manufacturers, and local governments

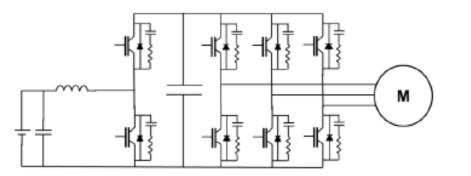
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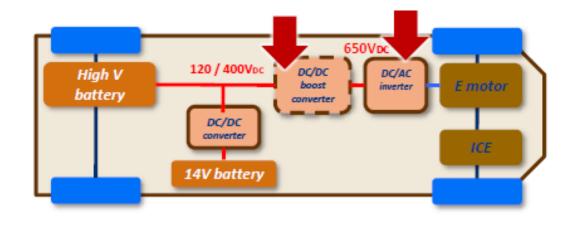


DC/AC inverter+ DC/DC booster option (full hybrid+ PHEV + BEV)

DC/AC Inverter:

- ✓ Generates a 3-phase AC signal from the high voltage battery DC current (200/400Vdc) to actuate the electric motor. The inverter is bidirectional.
- ✓ 400 -650 VAC
- ✓ Power: 20 –100 kW. Average power: 50 kW
- ✓ Water cooled with a dedicated cooling circuit
- ✓ Devices: IGBT + diodes





DC/DC booster: option :

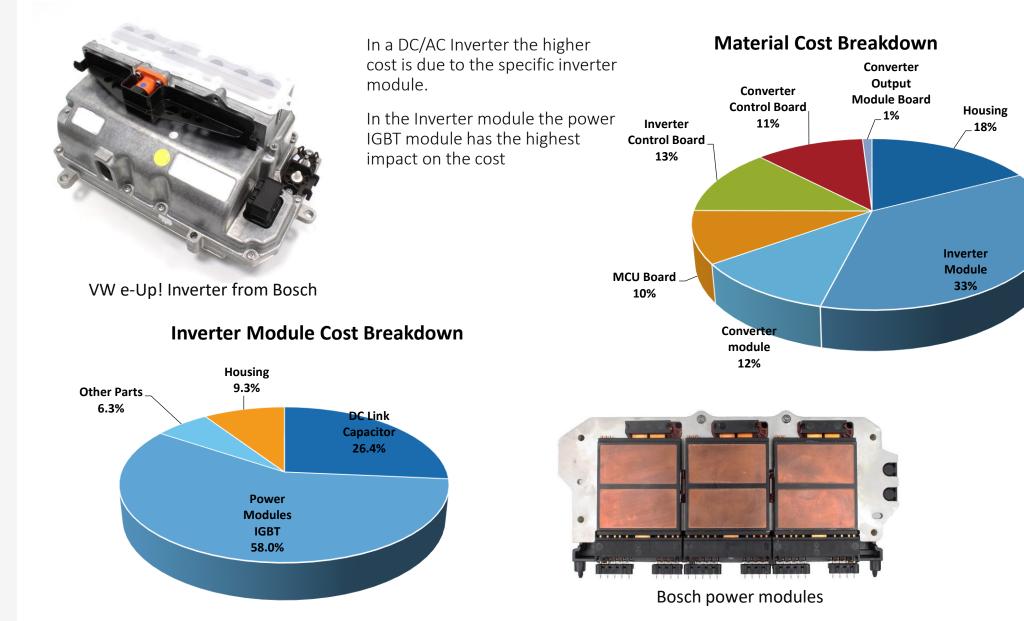
- ✓ Boosts the battery DC current (200/400Vdc) to provide higher voltage(600/650V) to the inverter. The converter is bi-directional. The booster is integrated in the same packaging as the inverter (Toyota Prius configuration).The booster allows the reduction of the overall powertrain cost.
- ✓ 400 -650 VAC
- ✓ Power: 20 –100 kW
- ✓ Water cooled
- ✓ Devices: IGBT + diodes







DC/AC Inverter Average Cost Breakdown

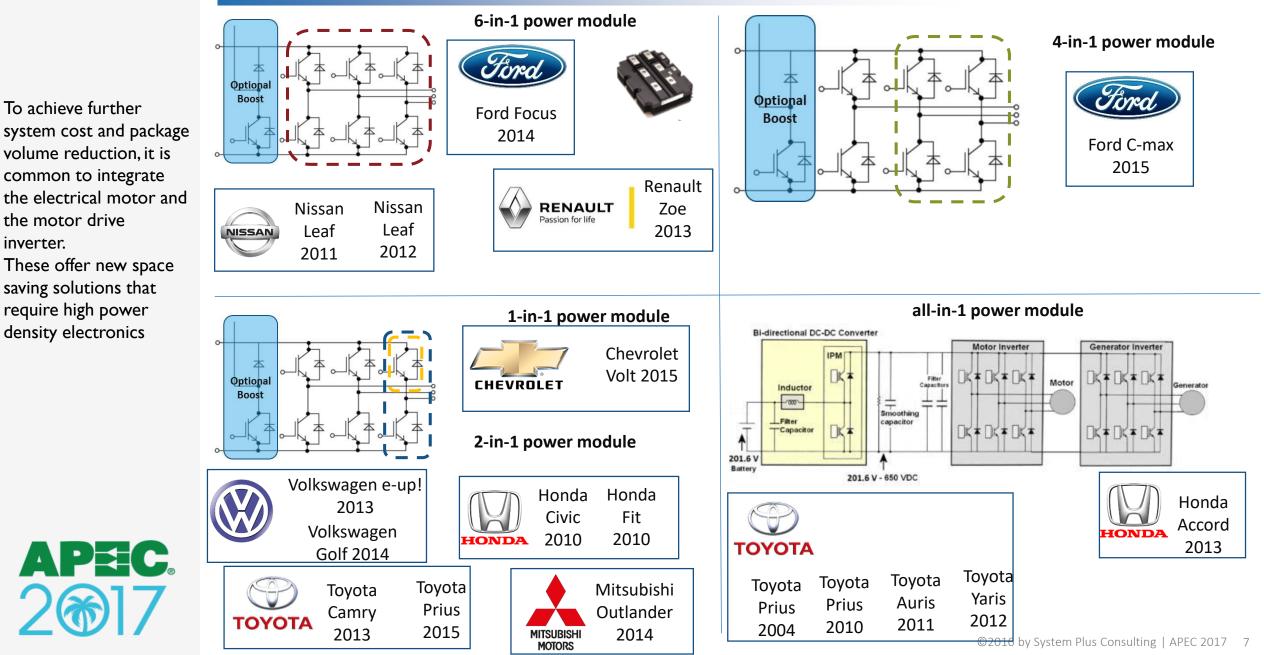


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inverter.

POWER MODULE IGBT LEVEL: different integration





Toyota and Honda integrates several converters together in a central box (motor inverter + generator

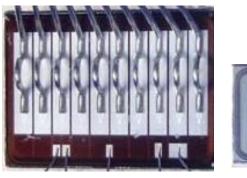
- inverter + boost + low
- voltage DC/DC):
- ✓ Shared cooling systems
- Semiconductors from different conversion stages sharing a power module
- ✓ Reduction of wire connection.



All-in-1 solution: Toyota & Honda

Toyota Prius:

- ✓ Motor inverter, generator and boost have different die sizes
- $\checkmark~$ Evolution of IGBT and Diode size and design



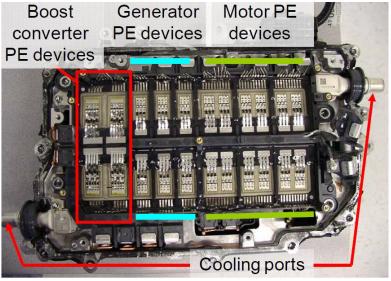
Toyota Prius II (2004)

HISTORY OF TOYOTA IGBTS FOR HVS						
Item		The 1st generation	The 2nd generation	The 3rd generation		
Chip appearance						
Device structure	Gate	Planar	Planar	Trench		
	Vertical	PT	PT	Thin wafer		
	Lifetime control	He irradiation	He irradiation	None		
Chip size (The 1st generation=1)		1	0.79	0.65		
Chip thickness (µm)		380	380	165		
Chip the	chess (µm)	580	580	105		

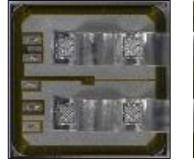


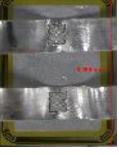
Toyota Prius III (2010)

	Generato	Generator Inverter	
	IGBT size	Diode size	
Prius II – 2 nd gen	131	40	
Prius III – 3 rd gen	108	67.5	
Prius IIIc – 3 rd gen	86.5	63.4	



Toyota Prius III (2010)





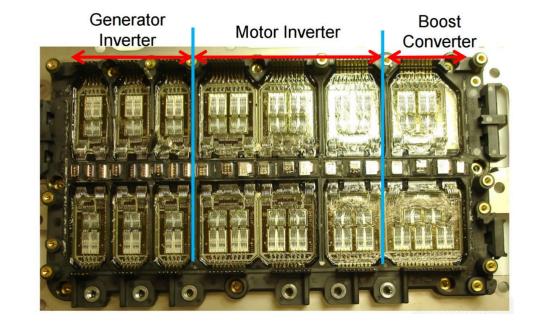
Toyota Prius IIIc (2011)

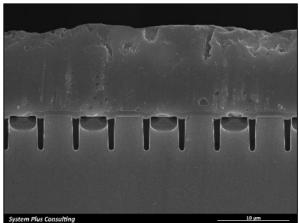
All-in-1 solution: Toyota & Honda

Honda Accord:

- ✓ Motor, generator and boost have the same dies
- ✓ IGBT size: 15.26x12.25 mm
- ✓ Diode size: 11.07x12.18mm









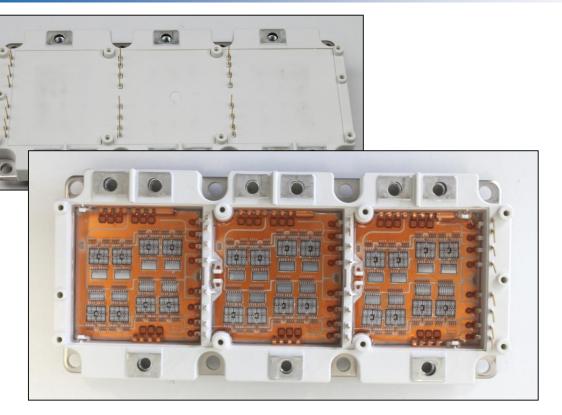


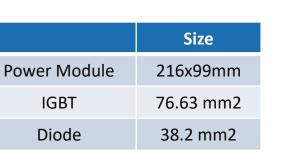


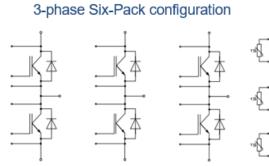
6-in-1 solution: Infineon

- The standard solution for power module is the 6in-1 module.
- Infineon proposes a solution with:
- ✓ 100kW continuous power
- ✓ 4 IGBT & FWD for configuration
- ✓ 650V/150A IGBT & diode

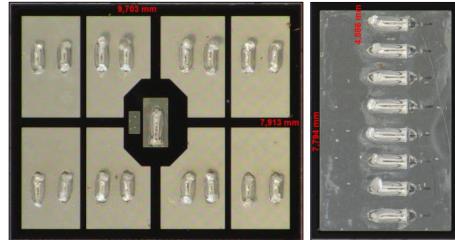
APEC

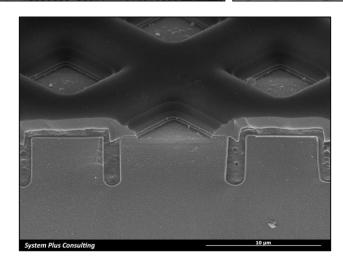






V_{CES} = 650V I_{C nom} = 600A / I_{CRM} = 1200A







2-in-1 solution: Toyota Prius IV 2015

For the 4th generation of Prius, Toyota proposes a completely different inverter structure with 2in-1 power module integrated in a specific modulable cooling system.

The PCU groups the inverter + DC/DC boost converter + generator AC/DC + DC/DC stepdown converter in one box.



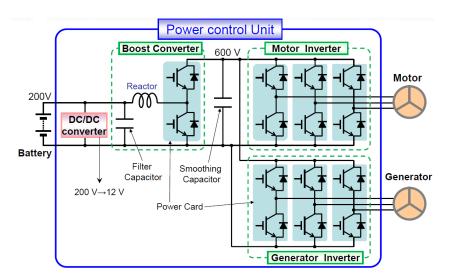


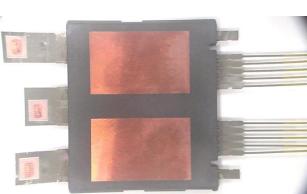
✓ Dooble side cooling

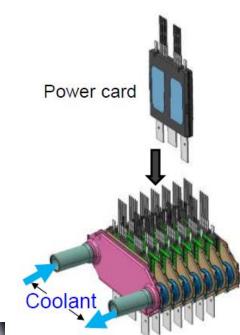
This structure allows a 35% of reduction of PCU size:

- ✓ Reduction of IGBT size
- ✓ Thickness of DC-DC converter reduced







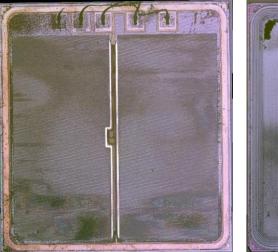


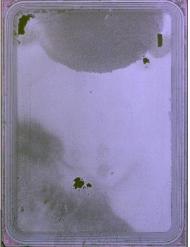


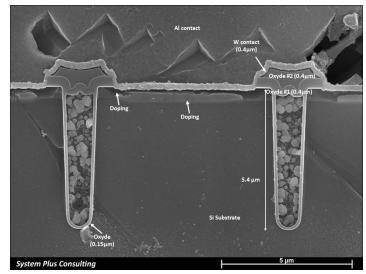
2-in-1 solution: Toyota Prius 2015

Toyota improves its device design allowing of a miniaturization of the dies

		Generator Inverter		
	Techno	IGBT size	Diode size	
Prius II – 2 nd gen	Planar	131	40	- 17% /+409
Prius III – 3 rd gen	Trench	108	67.5	- 17% /+40% - 20% /-6%
Prius IIIc – 3 rd gen	Trench	86.5	63.4	
Prius IV- 4 th gen	Trench	78.3	60.9) - 9% /-4%







FS Trench IGBT technology

Emitter plate Collector plate





2-in-1 solution: Bosch

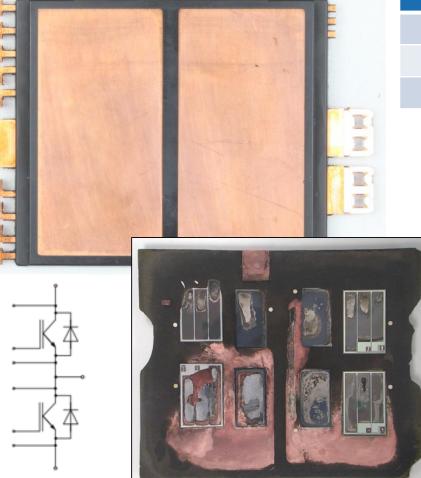
Bottom Copper Leadframe – 3.14mm

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Bosch proposes for the VW e-Up! A 2-in-1

solution:

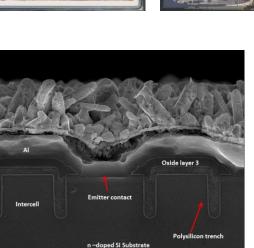
- ✓ 2IGBT & 2 diodes for configuration
- ✓ FS Trench IGBT of Infineon
- ✓ Molded package
- Chip on massive copper substrate
- ✓ Temperature sensor inside the package
- $\checkmark\,$ Thin film insulator



	Size	
Power Module	65x56mm	
IGBT	150 mm2	
Diode	98.5 mm2	

Top Solder SAC – 120µm





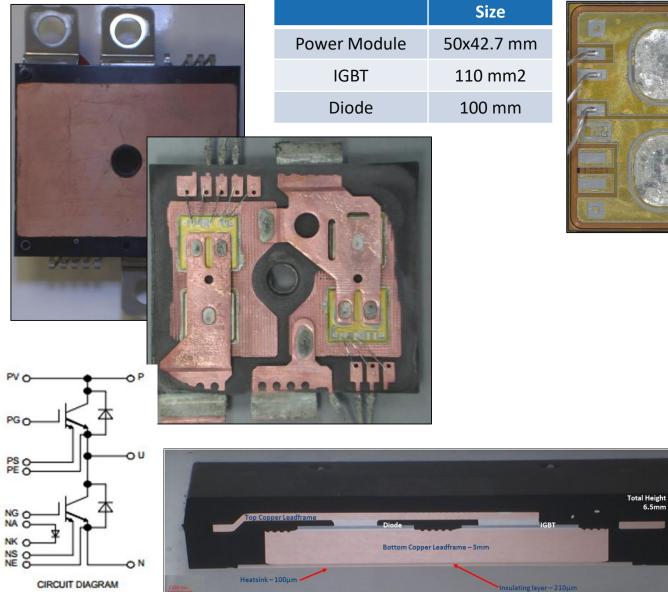




2-in-1 solution: Mitsubishi for Honda Fit

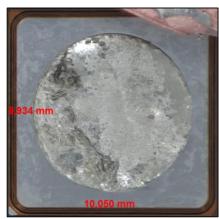
- Mitsubishi Electric was one of the first companies to offer double-side cooled modules for automotive applications
- ✓ 600V/300A capability
- ✓ Molded package

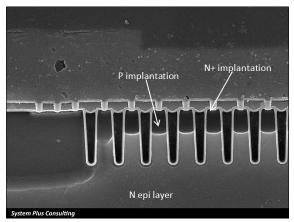






6 5mm



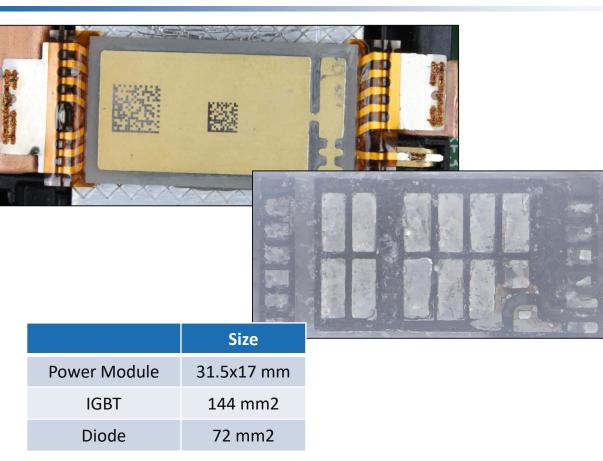


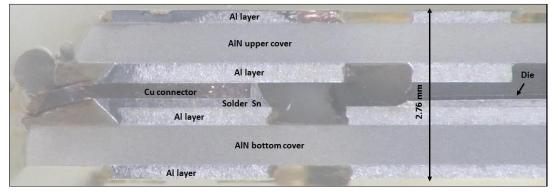
Mitsubishi CTSTB IGBT technology

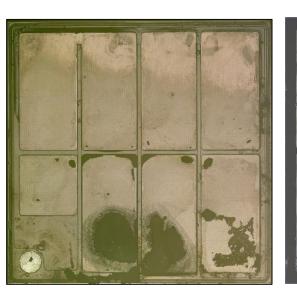
1-in-1 solution: Viper for Chevrolet Volt

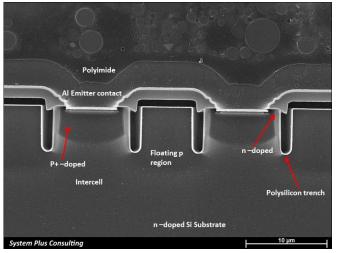
- The Viper module in Chevrolet Volt is using double side cooling in a one-in-one package:
- ✓ Wirebond-less package with sintered packaging interconnections.
- ✓ Small size
- ✓ Ceramic covers







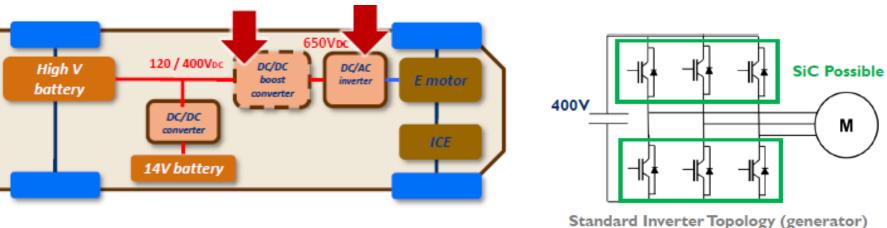




IR FS Trench IGBT technology

SiC integration

With an increase in power and the necessity of miniaturization, WBG materials could replace Si-based IGBT and MOSFETs in EV/HEV applications.

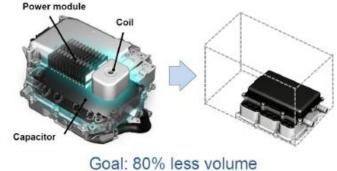


Standard Inverter Topology (generat

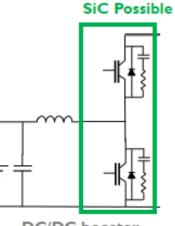
650V and 1200V IGBTs can be used in electric cars.

A DC/DC booster option can be added for full hybrid, PHEV and BEV and it needs an increase of IGBT voltages

According to Toyota, SiC power devices allow increased fuel efficiency and reduced PCU size up to 80%.



Courtesy of Toyota



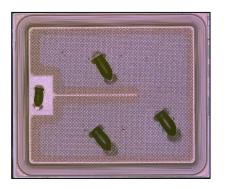
DC/DC booster





1200V Si IGBT and SiC MOSFET: size

SiC and Trench structure allows a reduction of the die size.

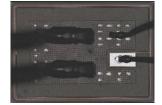


IXYS PT planar

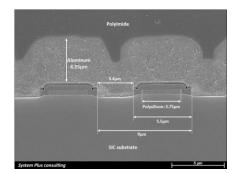


Infineon FS Trench

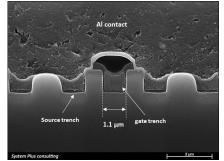




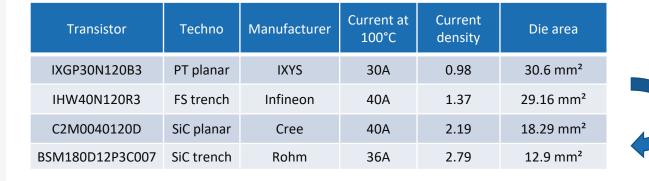
Wolfspeed SiC Planar



Rohm SiC Trench







55%

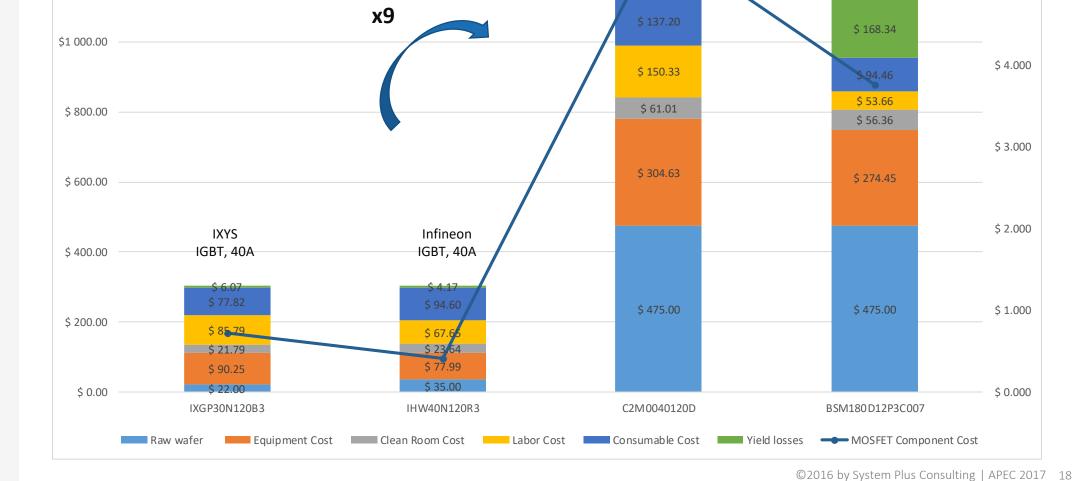
Si IGBT vs SiC MOSFET: cost

\$1 400.00

\$1 200.00

SiC dies are still very expensive comparing to Si-based dies

SYSTEMPIUS CONSULTING



Wafer cost breakdown

Cree

MOSFET, 40A

146.60

\$ 6.000

\$ 5.000

\$4.000

\$ 3.000

\$ 2.000

\$ 1.000

\$ 0.000

Rohm

MOSFET, 36A



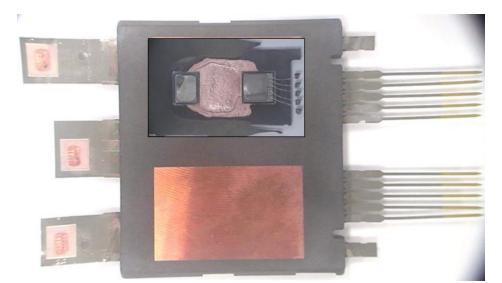


SiC power module impact

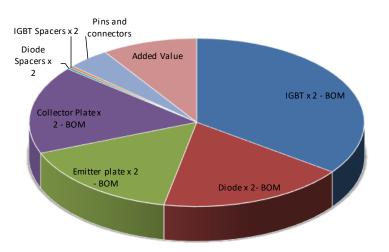
The implementation of SiC dies in EV/HEV modules should be driven by evident electrical performances and decrease of SiC

manufacturing cost



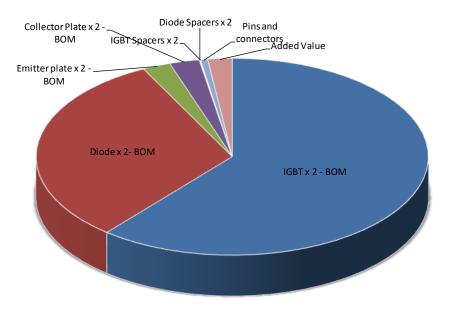


Module Breakdown Cost - Si



Considering the costs related to SiC dies and adapted packaging and, at the same time the size reduction of a complete power module; the SiC die cost will become predominant in the module breakdown.

Module Breakdown Cost -SiC





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